

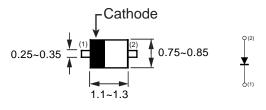
SCHOTTKY BARRIER DIODE

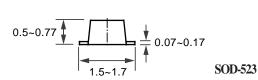
APPLICATION

• Low current rectification and high speed switching

FEATURE

- Extremely small surface mounting type. (SC-79/SOD-523)
- Io=200mA guaranteed despite size
- Low VF. (VF=0.40V Typ. at 200mA)





CONSTRUCTION

• Silicon epitaxial planar

MAXIMUM RATINGES (At TA = 25°C unless otherwise noted)

RATINGS	SYMBOL	DB2S31600L	UNITS
Maximum Recurrent Peak Reverse Voltage	Vrrm	30	Volts
Maximum RMS Voltage	Vrms	21	Volts
Maximum DC Blocking Voltage	VDC	30	Volts
Maximum Average Forward Rectified Current	lo	0.2	Amps
Peak Forward Surge Current at 8.3 mSec single half sine-wave	IFSM	1.0	Amps
Maximum Operating Temperature Range	TJ	+125	°C
Storage Temperature Range	Тѕтс	-40 to +125	°C

ELECTRICAL CHARACTERISTICS (At TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	DB2S31600L	UNITS
Maximum Instantaneous Forward Voltage at Ir= 200mA	VF	0.50	Volts
Maximum Average Reverse Current at Vr≈ 10V	lr	30.0	uAmps

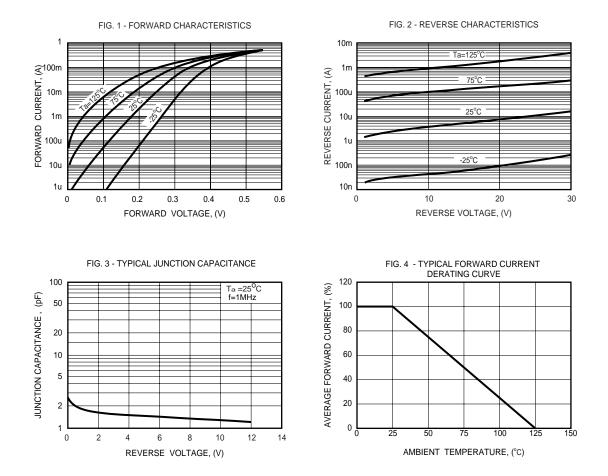
NOTES: 1. Measured at 1.0 MHz and applied reverse voltage of 1.0 volts. 2. ESD sensitive product handling required.

Ver.1.0





RATING CHARACTERISTIC CURVES (CH521S-30GP)



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